



### 80V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub> Tc = +25°C
80V	7.8mΩ @ V <sub>GS</sub> = 10V	92A

## **Description and Applications**

This new generation MOSFET is designed to minimize  $R_{DS(ON)}$  yet maintain superior switching performance. This device is ideal for use in power management and load switches.

- DC-DC converters
- Load switches

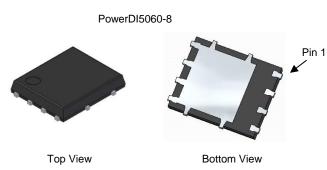
### **Features**

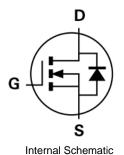
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production —
  Ensures More Reliable and Robust End Application
- High-Conversion Efficiency
- Low Rds(ON) Minimizes On-State Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- An automotive-compliant part is available under separate datasheet (<u>DMTH8008SPSQ</u>)

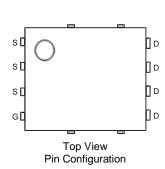
### **Mechanical Data**

- Package: PowerDI<sup>®</sup>5060-8
- Package Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
  Solderable per MIL-STD-202, Method 208 <a>3</a>
- Weight: 0.097 grams (Approximate)

Site 1:







Site 2:

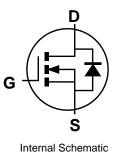
PowerDI5060-8/SWP (Type UX)

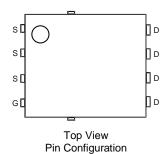


Top View



**Bottom View** 





Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



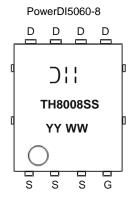
## Ordering Information (Note 4)

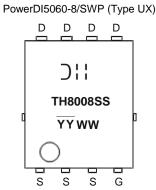
Part Number	Package	Packing		
Fait Number	Fackage	Qty.	Carrier	
DMTH8008SPS-13	PowerDI5060-8	2500	Tape & Reel	
DWITH00083F3-13	PowerDI5060-8/SWP (Type UX)	2500	Tape & Reel	

Note:

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**





⊃¦¦ = Manufacturer's Marking TH8008SS = Product Type Marking Code YYWW or YYWW = Date Code Marking YY or YY = Year (ex: 23 = 2023) WW = Week (01 to 53)

### **Maximum Ratings** (@Tc = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	80	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current, V <sub>GS</sub> = 10V (Note 5)	Steady State	$T_C = +25$ °C $T_C = +100$ °C	ΙD	92 65	А
Maximum Continuous Body Diode Forward Current (Note 5)			Is	83	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	360	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			Ism	360	Α
Avalanche Current, L = 0.1mH (Note 6)			las	40	Α
Avalanche Energy, L = 0.1mH (Note 6)			Eas	80	mJ

## Thermal Characteristics ( $@T_C = +25^{\circ}C$ , unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 7)	T <sub>A</sub> = +25°C	PD	1.6	W
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	RθJA	95	°C/W
Total Power Dissipation (Note 8)	$T_A = +25$ °C	PD	3.4	W
Thermal Resistance, Junction to Ambient (Note 8)	Steady State	Reja	44	°C/W
Total Power Dissipation (Note 5)	$T_C = +25$ °C	P <sub>D</sub>	100	W
Thermal Resistance, Junction to Case (Note 5)		Rejc	1.5	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +175	°C

Notes:

- ${\bf 5.}\ Thermal\ resistance\ from\ junction\ to\ soldering\ point\ (on\ the\ exposed\ drain\ pad).$
- 6.  $I_{AS}$  and  $E_{AS}$  ratings are based on low frequency and duty cycles to keep  $T_J = +25^{\circ}C$ .
- 7. Device mounted on FR-4 PCB, with minimum recommended pad layout, single sided.
- 8. Device mounted on FR-4 substrate PCB, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.



## **Electrical Characteristics** (@T<sub>C</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)	•					•	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	80	_	_	V	$V_{GS} = 0V$ , $I_D = 1mA$	
Zero Gate Voltage Drain Current	IDSS	_	_	1	μΑ	V <sub>DS</sub> = 64V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	Vgs(th)	2	_	4	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 1mA	
Static Drain-Source On-Resistance	D-s/s/s		6.5	7.8	mΩ	$V_{GS} = 10V, I_D = 14A$	
Static Dialii-Source Oil-Resistance	R <sub>DS(ON)</sub>		7.8	11	11122	$V_{GS} = 6V, I_D = 12A$	
Diode Forward Voltage	VsD		0.8	1.2	V	V <sub>G</sub> S = 0V, I <sub>S</sub> = 14A	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C <sub>iss</sub>		1950	_		V <sub>DS</sub> = 40V, V <sub>GS</sub> = 0V f = 1MHz	
Output Capacitance	Coss	—	826	_	pF		
Reverse Transfer Capacitance	Crss		56	_			
Gate Resistance	Rg		1.7	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 6V)	Qg	_	23	_			
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg		34	_	nC	V <sub>DS</sub> = 40V, I <sub>D</sub> = 14A	
Gate-Source Charge	Qgs		6	_	110		
Gate-Drain Charge	$Q_{gd}$		12	_			
Turn-On Delay Time	tD(ON)		8	_			
Turn-On Rise Time	t <sub>R</sub>		15	_	ns	$\begin{split} V_{DD} &= 40 V, \ V_{GS} = 10 V \\ I_D &= 14 A, \ R_g = 6 \Omega \end{split}$	
Turn-Off Delay Time	tD(OFF)	_	29	_	115		
Turn-Off Fall Time	t <sub>F</sub>	_	21				
Body Diode Reverse Recovery Time	t <sub>RR</sub>	_	43	_	ns	15 140 dl/dt 1000/u-	
Body Diode Reverse Recovery Charge	Qrr	_	49	_	nC	Is = 14A, dl/dt = 100A/µs	

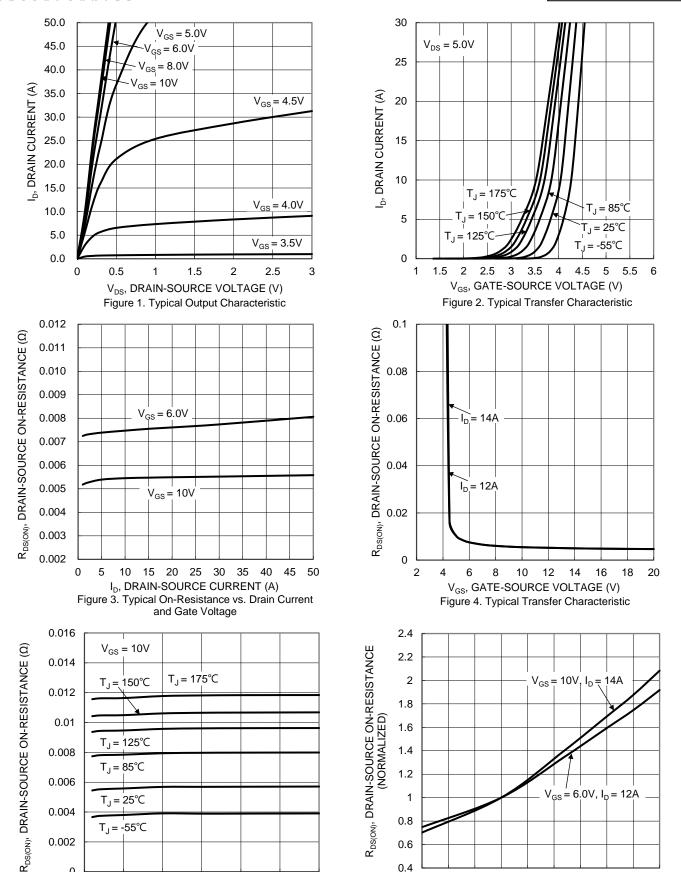
Notes:

<sup>9.</sup> Short duration pulse test used to minimize self-heating effect.

<sup>10.</sup> Guaranteed by design. Not subject to product testing.







I<sub>D</sub>, DRAIN CURRENT (A) Figure 5. Typical On-Resistance vs. Drain Current and Temperature

15

20

25

30

0.6 0.4

-50 -25 0 25 50 75

T<sub>J</sub>, JUNCTION TEMPERATURE (°C) Figure 6. On-Resistance Variation with

Temperature

100 125 150 175

0.002

0

0



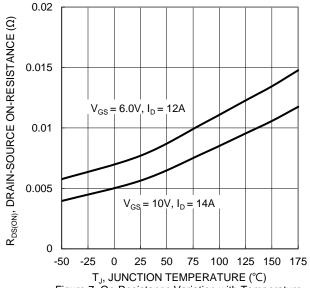
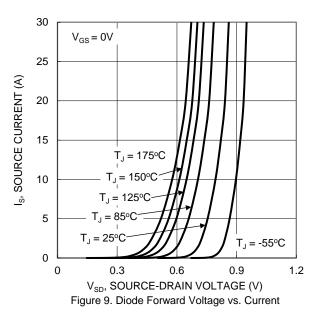


Figure 7. On-Resistance Variation with Temperature



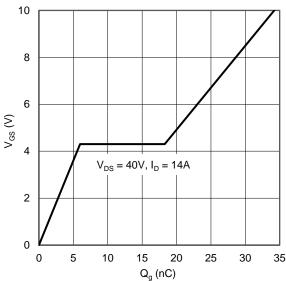


Figure 11. Gate Charge

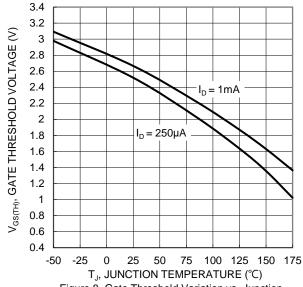
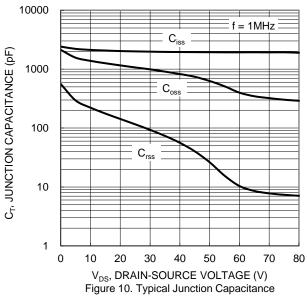


Figure 8. Gate Threshold Variation vs. Junction Temperature



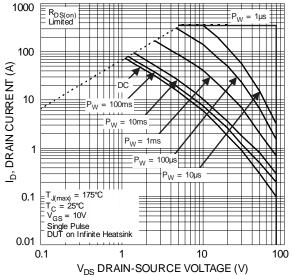


Figure 12 SOA, Safe Operation Area



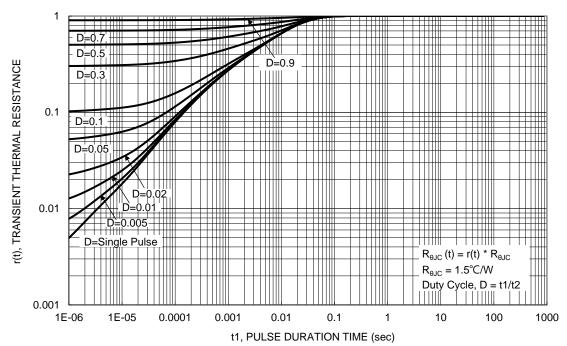


Figure 13. Transient Thermal Resistance



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

Detail A

### Site 1:

# 

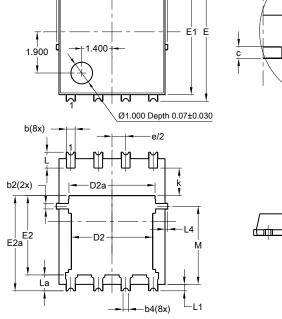
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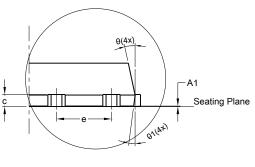
PowerDI5060-8				
Dim	Min	Max	Тур	
Α	0.90	1.10	1.00	
A1	0.00	0.05	-	
b	0.33	0.51	0.41	
b2	0.200	0.350	0.273	
b3	0.40	0.80	0.60	
С	0.230	0.330	0.277	
D		5.15 BSC	;	
D1	4.70	5.10	4.90	
D2	3.70	4.10	3.90	
D3	3.90	4.30	4.10	
E	(	6.15 BSC		
E1	5.60	6.00	5.80	
E2	3.28	3.68	3.48	
E3	3.99	4.39	4.19	
е		1.27 BSC	;	
G	0.51	0.71	0.61	
K	0.51	-	-	
L	0.51	0.71	0.61	
L1	0.100	0.200	0.175	
М	3.235	4.035	3.635	
M1	1.00	1.40	1.21	
Θ	10°	12°	11°	
Θ1	6°	8°	7°	
All Dimensions in mm				

Site 2:

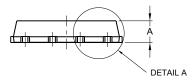
### PowerDI5060-8/SWP (Type UX)

PowerDI5060-8





DETAIL A



PowerDI5060-8/SWP (Type UX)				
Dim	Min	Max	Тур	
Α	0.90	1.10	1.00	
A1	0	0.05		
b	0.30	0.50	0.41	
b2	0.20	0.35	0.25	
b4	C	).25REF		
С	0.230	0.330	0.277	
D	5	.15 BS0	$\sim$	
D1	4.70	5.10	4.90	
D2	3.56	3.96	3.76	
D2a	3.78	4.18	3.98	
Е	6	.40 BS0		
E1	5.60	6.00	5.80	
E2	3.46	3.86	3.66	
E2a	4.195	4.595	4.395	
е	1	.27BSC	)	
k	1.05			
L	0.635	0.835	0.735	
La	0.635	0.835	0.735	
L1	0.200	0.400	0.300	
L1a	0.050REF			
L4	0.025	0.225	0.125	
М	3.205	4.005	3.605	
θ	10°	12°	11°	
θ1	6°	8°	7°	
All Dimensions in mm				

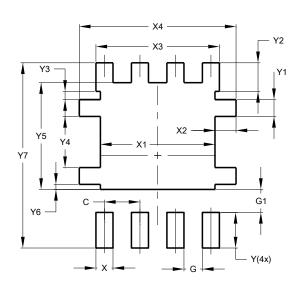


## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

Site 1:

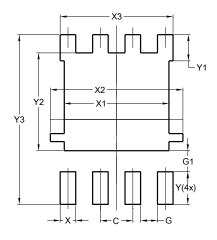
### PowerDI5060-8



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
Х	0.610
X1	4.100
X2	0.755
Х3	4.420
X4	5.610
Υ	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

Site 2:

### PowerDI5060-8/SWP (Type UX)



Dimensions	Value (in mm)		
С	1.270		
G	0.660		
G1	0.820		
Х	0.610		
X1	4.100		
X2	5.190		
Х3	4.420		
Υ	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



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